Vishay Semiconductors

www.vishay.com





LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS					
I _{F(AV)}	2 x 8 A				
V _R	200 V				
V _F at I _F	0.77 V				
t _{rr}	27 ns				
T _J max.	175 °C				
Package	SMPD (TO-263AC)				
Circuit configuration	Common cathode				

FEATURES

• Hyperfast recovery time, reduced Q_{rr}, and soft recovery



FREE

- 175 °C maximum operating junction temperature
- · Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, telecom, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

MECHANICAL DATA

Case: SMPD (TO-263AC)

Molding compound meets UL 94 V-0 flammability rating Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage		V _{RRM}		200	V		
Average restified forward average	per device		T _{solder pad} = 155 °C	16	٨		
Average rectified forward current	per diode	IF(AV)		8			
Non-repetitive peak surge current			T 05 °C 6 mg aguara pulas 190	А			
Non-repetitive peak surge current	per diode	IFSM	$T_J = 25 \ ^{\circ}C$, 6 ms square pulse	100			

ELECTRICAL SPECIFICATIONS ($T_J = 25 \ ^{\circ}C$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	200	-	-		
Forward voltage, per diode		I _F = 8 A	-	0.93	1.03	V	
		I _F = 8 A, T _J = 150 °C	-	0.77	0.87		
Devenue la classe commento a condicada	I _R	$V_{R} = V_{R}$ rated	-	-	2		
Reverse leakage current, per diode		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	6	100	μΑ	
Junction capacitance, per diode	CT	V _R = 200 V	-	23	-	pF	

Revision: 21-Jan-2021

1

Document Number: 95812

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



www.vishay.com

Vishay Semiconductors

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}$	õs, V _R = 30 V	-	27	-	
Bayaraa raaayary tima	+	$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr}$	-	-	25		
Reverse recovery time	t _{rr}	T _J = 25 °C		-	23	-	ns
		T _J = 125 °C	$I_F = 8 A,$	-	35	-	
Pools recovery ourrent	I _{RRM}	T _J = 25 °C		-	2.8	-	Α
Peak recovery current		T _J = 125 °C	dl _F /dt = 200 A/µs, V _B = 160 V	-	5	-	~
Deverse version shows	0	T _J = 25 °C		-	30	-	nC
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	90	-	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	+175	°C	
Thermal resistance, per diode junction to mount	R _{thJM}		-	1.8	2.5	°C/W	
Approximate weight				0.55		g	
Approximate weight				0.02		oz.	
Marking device		Case style SMPD (TO-263AC)		16CI	DH02		



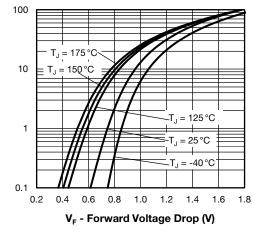


Fig. 1 - Typical Forward Voltage Drop Characteristics

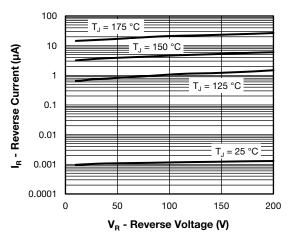


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

Vishay Semiconductors

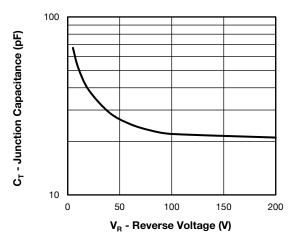


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

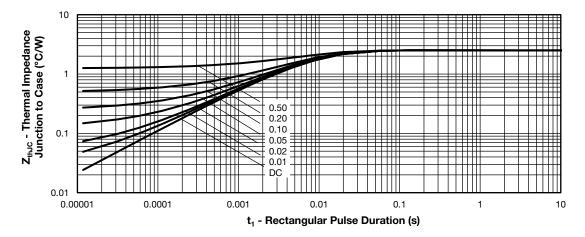
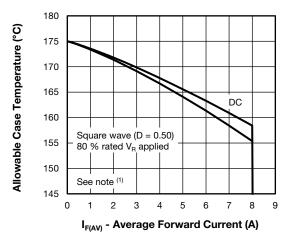
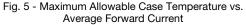


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



www.vishay.com



Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mbox{Pd} = \mbox{Forward power loss} = \mbox{I}_{F(AV)} \times \mbox{V}_{FM} \mbox{ at } (\mbox{I}_{F(AV)}/\mbox{D}) \mbox{ (see fig. 5);} \\ \mbox{Pd}_{REV} = \mbox{Inverse power loss} = \mbox{V}_{R1} \times \mbox{I}_{R} \mbox{ (1 - D); } \mbox{I}_{R} \mbox{ at } \mbox{V}_{R1} = \mbox{rated} \mbox{V}_{R} \end{array}$

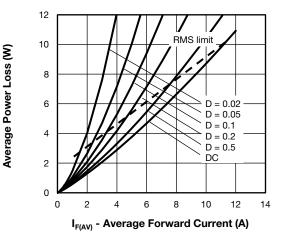


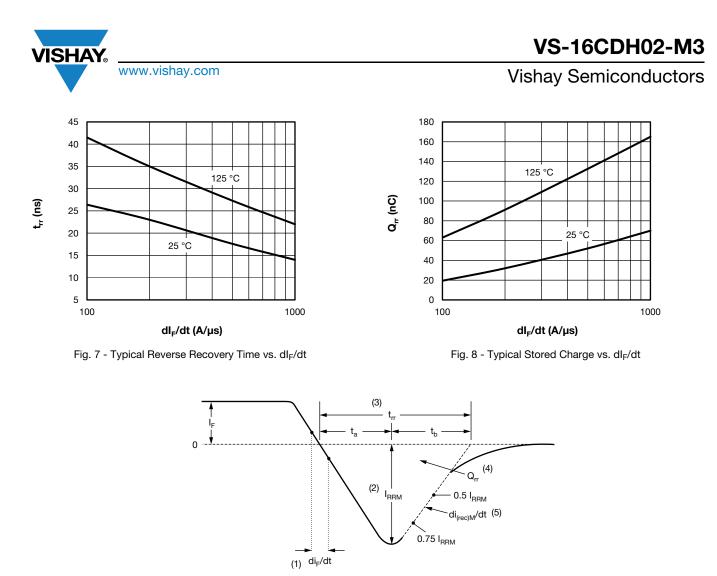
Fig. 6 - Forward Power Loss Characteristics

Revision: 21-Jan-2021

3

Document Number: 95812

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>





- (2) I_{RRM} peak reverse recovery current
- (3) $t_{\rm rr}$ reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (5) di_{(rec)M}/dt peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

Vishay Semiconductors

www.vishay.com

SHAY

ORDERING INFORMATION TABLE

Device code	VS-	16	С	D	н	02	-M3
201100 0000			•			02	
	1	2	3	4	5	6	7
	1	- Visł	nay Sem	nicondu	ctors pr	oduct	
	2	- Cur	rent rati	ng (16 A	A)		
	3	- Circ	cuit conf	figuratio	n:		
		C =	commo	on catho	de		
	4	- D =	SMPD	packag	e		
	5	- Pro	cess typ	be,			
		H =	hyperfa	ast recov	very		
	6	- Volt	tage coo	de (02 =	200 V)		
	7	M3	3 = halo	gen-free	e, RoHS	-compli	iant, and

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER REEL MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-16CDH02-M3/I	2000	2000	13" diameter plastic tape and reel				

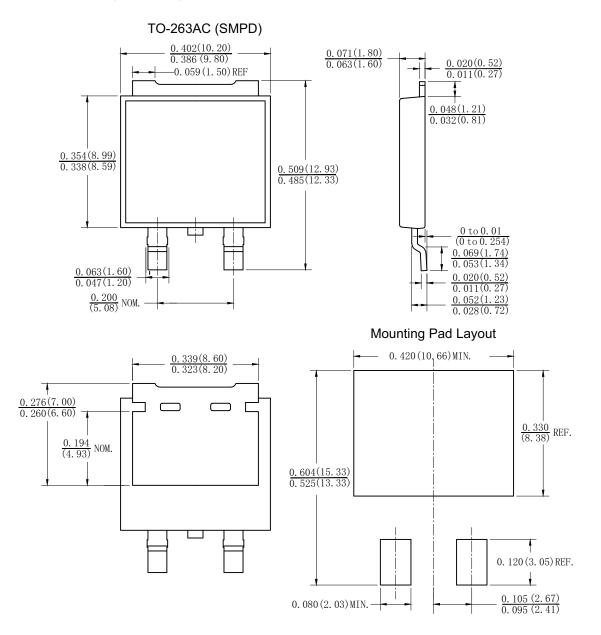
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95604				
Part marking information	www.vishay.com/doc?95566				
Packaging information	www.vishay.com/doc?88869				





TO-263AC (SMPD)

DIMENSIONS in inches (millimeters)





Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Vishay products are not designed for use in life-saving or life-sustaining applications or any application in which the failure of the Vishay product could result in personal injury or death unless specifically qualified in writing by Vishay. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

© 2025 VISHAY INTERTECHNOLOGY, INC. ALL RIGHTS RESERVED

Revision: 01-Jan-2025

1